REMARKS

Claim Rejections Under 35 U.S.C. § 102

Claims 1 and 3-6 were rejected under 35 U.S.C. § 102(e) as being anticipated by *Chang et al.* (U.S. Patent No. 6,754,105). Applicant respectfully traverses this rejection.

In the interest of expediency, claim 1 has been amended to include the allowable limitations of claim 2. Applicant believes that claim 1 is now in condition for allowance.

Since Applicant believes that claim 1 is now allowable, the dependent claims that depend from claim 1 are also now allowable. Applicant thus respectfully requests reconsideration and withdrawal of the rejection and allowance of claims 1 and 3 – 6.

Chang et al. teaches a flash memory device comprised of trench side wall charge trapping. Each trench has a single bit line 62 formed under each trench 46. *Chang et al.* also discloses a dielectric layer 58 formed between each bit line 62 and the dielectric filled trench 46. *Chang et al.* neither teaches nor suggests Applicant's invention as claimed.

Applicant claims a plurality of active areas substantially adjacent to the first and second sides of the trench. *Chang et al.* discloses a single bit line that wraps around both sides of the trench. The structure and function of Applicant's active areas is neither taught nor suggested by *Chang et al.*

Allowable Subject Matter

Claim 2 was objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form, including all of the limitations of the base claim and any intervening claims. Applicant has amended claim 1 as suggested by the Examiner to include the allowable limitations of claim 2. Claim 2 has been canceled to avoid duplication of claimed subject matter.

Claims 7-10 and 25-34 were allowed.

Information Disclosure Statement Form PTO-1449

Applicant notes that examiner failed to initial two references on Page 3 of the Information Disclosure Statement Form PTO-1449 that was filed on May 14, 2004 (copy attached). Applicant requests that Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

CONCLUSION

For the above-cited reasons, Applicant respectfully requests that the Examiner allow the claims of the present application. If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211. No new matter has been added and no additional fee is required by this amendment and response.

Respectfully submitted,

Date: 5/17/05

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First Named Inventor	Michael Smith
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INFORMATION DISCLOSURE STATEMENT FORM PTO-1449

Title: TRENCH CORNER EFFECT BIDIRECTIONAL FLASH MEMORY CELL

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	Examiner Cuong Q. Nguyen	Art Unit 2811	Page 1 of 1

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